

Data Sheet

October 1998

专业PCB打样工厂

File Number 2257.1

, 24小时加急出货 BUZ45

9.6A, 500V, 0.600 Ohm, N-Channel Power MOSFET

IThis is an N-Channel enhancement mode silicon gate power field effect transistor designed for applications such as switching regulators, switching converters, motor drivers, relay drivers, and drivers for high power bipolar switching transistors requiring high speed and low gate drive power. This type can be operated directly from integrated circuits.

Formerly developmental type TA17435.

Ordering Information

PART NUMBER	PACKAGE	BRAND
BUZ45	TO-204AA	BUZ45

NOTE: When ordering, use the entire part number.

Features

捷多邦,

- 9.6A, 500V
- $r_{DS(ON)} = 0.600\Omega$
- SOA is Power Dissipation Limited
- Nanosecond Switching Speeds
- Linear Transfer Characteristics
- High Input Impedance
- Majority Carrier Device

Symbol





